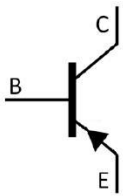


Silicon PNP transistor in a TO-92 Plastic Package.

High h_{FE} .

General amplifier application.



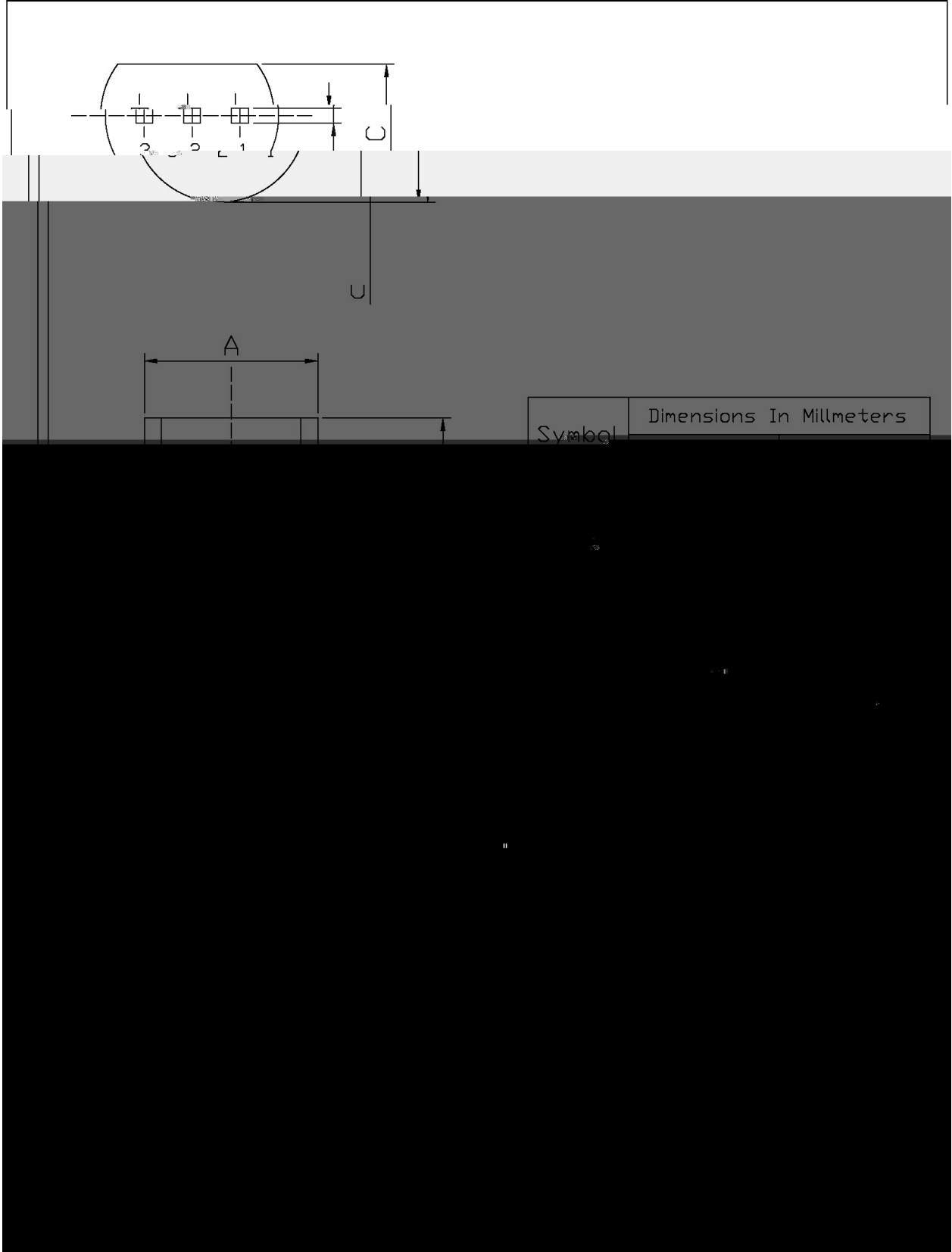
PIN 1 Base PIN 2 Collector PIN 3 Emitter

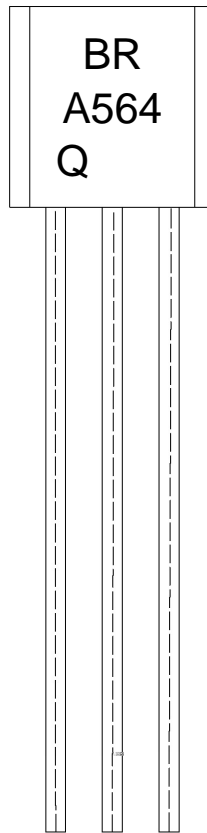
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	2SA564	-25	V
		2SA564A	-45	
Collector to Emitter Voltage	V_{CEO}	2SA564	-25	V
		2SA564A	-45	
Emitter to Base Voltage	V_{EBO}		-7.0	V
Collector Current - Continuous	I_C		-100	mA
Collector Current – Continuous(Pulse)	I_{CP}		-200	mA
Collector Power Dissipation	P_C		400	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-10V$ $I_E=0$		-0.001	-1.0	A
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-10V$ $I_B=0$			-10	A
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-10\mu A$ $I_E=0$	-25			V
			-45			
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10\mu A$ $I_E=0$	-25			V
			-45			
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10 A$ $I_C=0$	-5.0			V
DC Current Gain	h_{FE}	$V_{CE}=-10V$ $I_C=-2.0mA$	130	250	520	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-100mA$ $I_B=-10mA$		-0.3		V
Output capacitance	C_{ob}	$V_{CB}=-10V$ $f=1.0MHz$ $I_E=0$		3.5		pF

T0-92

Unit: mm





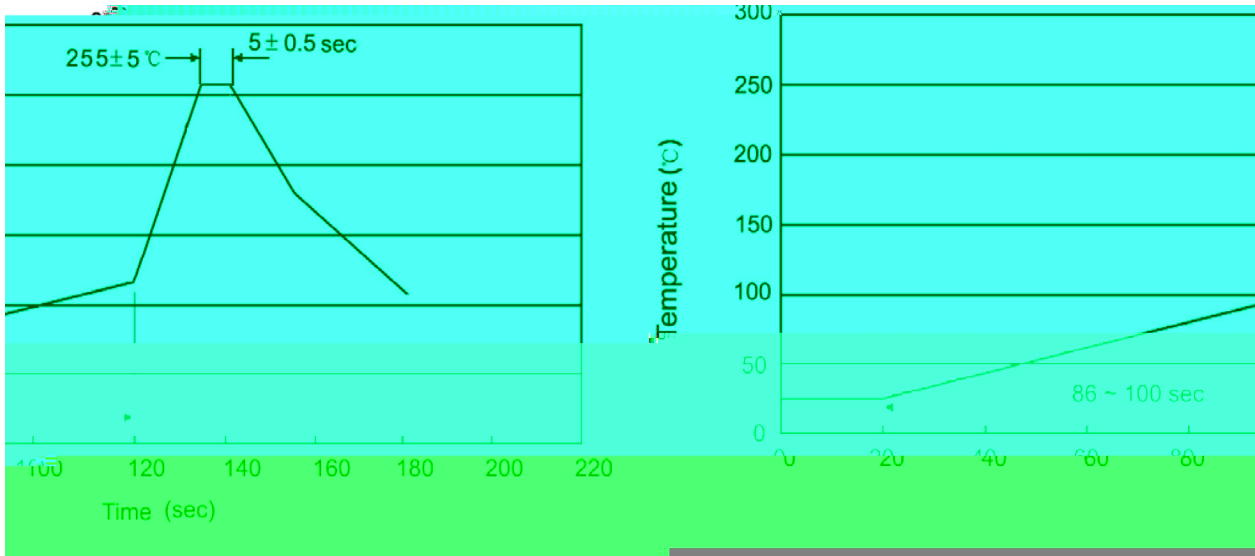
Note:

BR: Company Code.

A564: Product Type.

Q: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.


Note:

- 1 25 150 60 90sec;
- 2 255 5 5 0.5sec;
- 3 2 10 /sec.

- 1.Preheating:25~150 , Time:60~90sec.
- 2.Peak Temp.:255 5 , Duration:5 0.5sec.
3. Cooling Speed: 2~10 /sec.

270 5

10 1 sec.

Temp:270±5

Time:10±1 sec

/ BULK

Package Type	Units				Dimension		(unit mm ³)

/ AMMO

Package Type	Units				Dimension		(unit mm ³)